## Claims:

1. (Previously Amended) An apparatus for polishing a surface of a workpiece, the surface including a low dielectric constant material, comprising:

a platen configured to orbit about an axis at a speed up to about 2000 revolutions per minute;

- a polishing surface attached to the platen; and
- a workpiece carrier proximate the polishing surface.
- 2. (Previously Amended) The apparatus of claim 1, wherein the platen is configured to orbit at about 1000 orbits per minute.
- 3. (Original) The apparatus of claim 1, wherein the platen is further configured to dither.
- 4. (Previously Amended) The apparatus of claim 1, wherein the platen orbits with an orbital radius of about 0.25 to about 1 inch.
- 5. (Previously Amended) The apparatus of claim 1, wherein the carrier and the platen are configured to move the workpiece relative to the polishing surface at a speed of about 0.8 to about 3.2 meters per second.
- 6. (Original) The apparatus of claim 1, wherein the carrier is configured to apply about 0.25 to about 2 pounds per square inch pressure to the workpiece in the direction of the polishing surface.

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- 7. (Original) The apparatus of claim 1, wherein the platen includes channels configured to allow polishing solution to circulate through a portion of the platen.
- 8. (Original) The apparatus of claim 7, wherein the platen is configured to allow the polishing slurry to flow at a rate of about 120 to about 200 milliliters per minute.
- 9. (Original) The apparatus of claim 1, wherein the platen is configured to orbit at a speed of about 500 to about 2000 orbits per minute.
- 10. (Original) The apparatus of claim 1, wherein the carrier includes a bladder to regulate pressure applied to the workpiece.
- 11. (Original) The apparatus of claim 1, wherein the platen includes a conduit configured to allow heat exchange fluid to flow through a portion of the platen.
- 12. (Previously Amended) A polishing system for removing material from a wafer surface, the wafer including low-k material, comprising:

a plurality of polishing stations, wherein at least one of said plurality of polishing stations includes a platen configured to move at about 0.8 to about 3.2 meters per second relative to the wafer comprising low-k material;

a clean system including at least one clean station; and a load station.



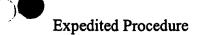


- 13. (Original) The polishing system of clam 12, further comprising a buff station.
- 14. (Original) The polishing system of claim 12, further comprising a carousel carrier apparatus including a plurality of workpiece carriers.
- 15. (Original) The polishing system of claim 14, wherein the plurality of workpiece carriers are configured to rotate about an axis and translate in a radial direction.
- 16. (Original) The polishing system of claim 14, wherein at least one of said plurality of workpiece carriers is configured to apply a about 0.25 to about 2 pounds per square inch to the workpiece in the direction of the platen.
- 17. (Original) The polishing system of claim 12, further comprising a workpiece carrier configured to rotate about an axis and apply about 0.25 to about 2 pounds per square inch to the workpiece in the direction of the platen.
- 18. (Original) The polishing system of claim 12, wherein the platen is configured to orbit.
- 19. (Original) The polishing system of claim 18, wherein the platen is configured to orbit with a radius of about 0.25 to about 1 inch.
- 20. (Original) The polishing system of claim 12, wherein the platen is configured to orbit about an axis at a speed of about 500 to about 2000 orbits per minute.



- 21. (Original) The polishing system of claim 12, further comprising a temperature control system configured to regulate a temperature of a polishing fluid.
- 22. (Original) The polishing system of claim 12, wherein the platen includes channels to allow polishing fluid to flow through a portion of the platen.
- 23. (Original) The polishing system of claim 12, wherein the platen includes a groove configured to allow heat exchange fluid to flow through a portion of the platen.
- 24. (Original) The polishing system of claim 12, further comprising a polishing surface attached to the platen, the polishing surface including apertures to allow polishing fluid to circulate through a portion of the polishing surface.
- 25. (Previously Amended) A polishing system for removing conductive material deposited onto low-k material, comprising:
  - a load and unload station;
- a plurality of polishing stations, wherein at least one polishing station includes a platen configured to move relative to a workpiece comprising low-k material at about 0.8 to about 3.2 meters per second and a workpiece carrier configured to apply about 0.25 to about 2 psi to a workpiece in the direction of the platen; and
  - a clean system proximate the plurality of polishing station.





26. (Previously Amended) A method for removing material from a surface of a workpiece, including low-k material, comprising the steps of:

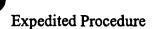
providing a workpiece comprising low-k material;

placing the workpiece comprising low-k material in contact with a polishing surface; and orbiting the polishing surface at a speed about 500 to about orbits per minute.

- 27. (Original) The method of claim 26, further comprising the step of rotating the wafer.
- 28. (Original) The method of claim 26, further comprising the step of applying about 0.25 to about 2 pounds per square inch to the workpiece in the direction of the polishing surface.
- 29. (Original) The method of claim 26, further comprising the step of circulating polishing fluid through a portion of the platen.
- 30. (Original) The method of claim 26, further comprising the step of regulating the temperature of the polishing surface.
- 31. (Original) The method of claim 26, further comprising the step of regulating the temperature of a polishing fluid.
- 32. (Previously Amended) An apparatus for polishing a surface of a workpiece, the surface including a low dielectric constant material, comprising:

a platen configured to move about an axis;





a polishing surface attached to the platen; and

a workpiece carrier proximate the polishing surface, wherein the platen and the workpiece carrier are configured such that the surface of the workpiece comprising a low dielectric constant material and the platen move at a relative speed of about 0.8 to about 3.2 meters per second.

33. (Previously Amended) A method for removing material from a surface of a workpiece, including low-k material, comprising the steps of:

providing a workpiece comprising low-k material;

placing the workpiece comprising low-k material in contact with a polishing surface; and moving the polishing surface and the workpiece comprising low-k material relative to each other at a speed of about 0.8 to about 3.2 meters per second.

